

Substitute for form 1449/A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>				Application No.	10/661,037
				Filing Date	September 12, 2003
				First Named Inventor	John D. Hyde
				Art Unit	2822
				Examiner Name	Ida M. Soward
Sheet	1	of	6	Attorney Docket Number	22524-17802

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